

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

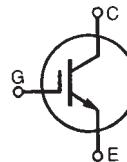
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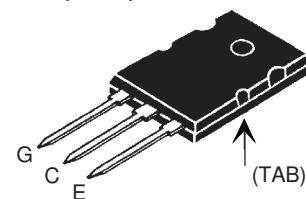
**HiPerFAST™ IGBT**  
**Lightspeed 2™ Series**
**IXGK 120N60C2**  
**IXGX 120N60C2**

$V_{CES}$	=	600	V
$I_{C110}$	=	120	A
$V_{CE(sat)}$	=	2.5	V
$t_{fi(ty)}$	=	45	ns

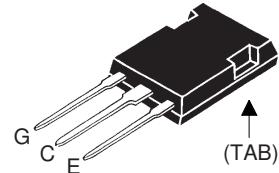


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ (limited by leads)	75	A
$I_{C110}$	$T_C = 110^\circ\text{C}$ (die limit)	120	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	500	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 4.7 \Omega$ Clamped inductive load @ $V_{CE} \leq 600 \text{ V}$	$I_{CM} = 200$	A
$P_c$	$T_C = 25^\circ\text{C}$	830	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS, $t = 1$ minute $I_{ISOL} < 1 \text{ mA}$ $t = 20$ seconds	2500 3000	V~ V~
$F_c$	Clamping force	20..120/4.5..25	N/ib
$T_L$	Maximum lead temperature for soldering (Note 3)	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 seconds	260	$^\circ\text{C}$
<b>Weight</b>	TO-264 PLUS247	10 5	g g

TO-264(IXGK)



PLUS247(IXGX)



G = Gate      C = Collector  
 E = Emitter      Tab = Collector

**Features**

- Very high frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on
  - drive simplicity

**Applications**

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

**Advantages**

- High power density
- Very fast switching speeds for high frequency applications
- High power surface mountable packages

Symbol	Test Conditions	Characteristic Values		
		( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Min.	Typ.
$BV_{CES}$	$I_C = 1 \text{ mA}$ , $V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 500 \mu\text{A}$ , $V_{CE} = V_{GE}$	3.0	5.0	V
$I_{CES}$	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$		100 2	$\mu\text{A}$ mA
		$T_J = 125^\circ\text{C}$		
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$		$\pm 200$	nA
$V_{CE(sat)}$	$I_C = I_T$ , $V_{GE} = 15 \text{ V}$ Note 1	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	2.1 2.0	2.5 V

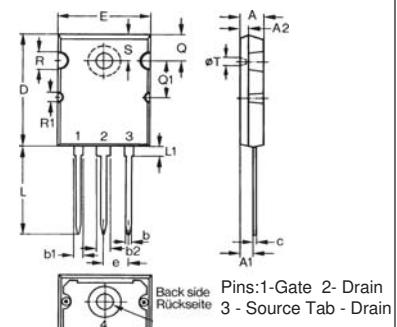
Symbol	Test Conditions	Characteristic Values			
		( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Min.	Typ.	Max.
$g_{fs}$	$I_C = 60 \text{ A}; V_{CE} = 10 \text{ V}$ , Note 1	50	75	S	
$C_{les}$			11	nF	
$C_{oes}$	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		680	pF	
$C_{res}$			190	pF	
$Q_g$			350	nC	
$Q_{ge}$	$I_C = I_T, V_{GE} = 15 \text{ V}, V_{CE} = 0.5 V_{CES}$		72	nC	
$Q_{gc}$			131	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 80 \text{ A}, V_{GE} = 15 \text{ V}$ $V_{CE} = 400 \text{ V}, R_G = R_{off} = 1.0 \Omega$	18	ns		
$t_{ri}$		25	ns		
$t_{d(off)}$		95	150	ns	
$t_{fi}$		45	ns		
$E_{off}$		0.9	1.6	mJ	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 80 \text{ A}, V_{GE} = 15 \text{ V}$ $V_{CE} = 400 \text{ V}, R_G = R_{off} = 1.0 \Omega$	18	ns		
$t_{ri}$		25	ns		
$E_{on}$		1.6	mJ		
$t_{d(off)}$		130	ns		
$t_{fi}$		85	ns		
$E_{off}$		1.5	mJ		
$R_{thJC}$			0.15	K/W	
$R_{thJC}$			0.15	K/W	

Note: 1. Pulse test,  $t \leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ ;

2. Test current  $I_T = 100 \text{ A}$ ;

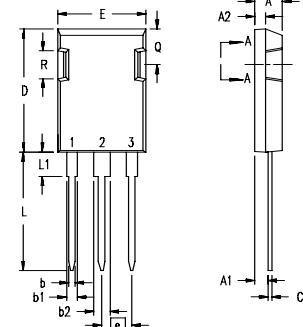
3. Temperature measured at 1.6 mm (0.062 in.) from case for 10 seconds

### TO-264 AA Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	.1020	.1030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

### PLUS 247™ (IXGX) Outline



Terminals:  
1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405B2 6,759,692 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2